

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

APPLICANT

Lukanc et al.

FILING DATE

12/11/2001

GROUP ART UNIT

Unknown

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE
AR	A1	6,410,193	6/25/2002	Stivers et al.	430	5	
	A2	6,013,399	1/11/00	Nguyen	430	5	
	A3	5,861,233	1/19/99	Sekine et al.	430	296	
	A4	5,780,187	7/14/98	Pierrat	430	1051700	
	A5	5,641,593	6/24/97	Watanabe et al.	430	5	
	A6	5,619,059	4/8/97	Li et al.	257	431	
AR	A7	5,328,784	7/12/1994	Fukuda	430	5	

FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION
AR	A8	EP 0 708 367 B1	14-01-1998	European		YES NO


OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

AR	A9	T. BRUNNER ET AL., "170 nm gates fabricated by phase-shift mask and top anti-reflector process," 182/SPIE Vol. 1927, Optical/Laser Microlithography VI, 1993, pps. 1-8.
	A10	KURT RONSE ET AL., "Comparison of various phase shift strategies and application to 0.35 μ m ASIC Designs," 2/SPIE Vol, 1927, Optical/Laser Microlithography VI, 1993, pps. 1-15.
	A11	J. M. CALVERT ET AL., "Projection X-Ray Lithography With Ultrathin Imaging Layers and Selective Electroless Metallization," Optical Engineering Vol. 32 No. 10, Oct. 1993., pp. 2437-2445
	A12	H. KYURAGI ET AL., "Synchrotron Radiation-Excited Chemical Vapor Deposition of Silicon Nitride Films from a SiH ₄ + NH ₃ Gas Mixture," Journal of the Electrochemical Society, Vol. 138 No. 11, Nov. 1991, pp. 3412-3416.
AR	A13	Y. MATSUI ET AL., "Low-Temperature Growth of SiO ₂ Thin Film by Photo-Induced Chemical Vapor Deposition Using Synchrotron Radiation," Japanese Journal of Applied Physics, Part I, Vol. 31 n.6B, June 1992, pp. 1972-1978.

EXAMINER


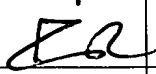
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Form PTO-1449 (MODIFIED)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. 039153-0448 (G1153)	SERIAL NO. 10/016,710
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	B14	J. F. MOORE ET AL., "Deposition of Dielectric Thin Films by Irradiation of Condensed Reactant Mixtures," Materials Research Society Symposium Proceedings, Vol. 335, 1994, pp. 81-86.
	B15	I. NISHIYAMA ET AL., "Photon Energy Dependence of Synchrotron Radiation Induced Growth Suppression and Initiation in Al Chemical Vapor Deposition II. Surface Analysis by Auger Electron Spectroscopy," Applied Surface Science, Vol. 103, 1996, pp. 299-306
	B16	O. R. WOOD II ET AL., "Use of Attenuated Phase Masks in Extreme Ultraviolet Lithography," Journal of Vacuum Science and Technology B, Vol. 15, No. 6, Nov/Dec 1997, pp. 2448-2451
	B17	R. ZANONI ET AL., "Synchrotron-Radiation-Stimulated Tungsten Deposition on Silicon from W(CO) ₆ ," Journal of Vacuum Science and Technology A, Vol. 9, No. 3, May/June 1991, pp. 931-934.
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